

AMENDMENTS TO THE CLAIMS:

Please amend the claims as indicated in listing of claims provided below. This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A method for producing a semiconductor device ~~characterized by having a step of~~ comprising:

forming wiring using a first solution ~~ejection means~~ ejector for ejecting a conductive material,

~~a step of~~ forming a resist mask on the wiring using a second solution ~~ejection means~~ ejector, and

~~a step of~~ etching the wiring using an atmospheric-pressure plasma device having a linear plasma ~~generation means~~ generator using the resist mask as a mask.

2. (Currently Amended) A method for producing a semiconductor device ~~characterized by having a step of~~ comprising:

forming wiring using a solution ~~ejection means~~ ejector for ejecting a conductive material,

~~a step of~~ forming a resist mask at least on the wiring, and

~~a step of~~ etching the wiring using an atmospheric-pressure plasma device having a linear plasma ~~generation means~~ generator using the resist mask as a mask.

3. (Currently Amended) A method for producing a semiconductor device ~~characterized by having a step of~~ comprising:

forming wiring,

~~a step of~~ forming a resist mask at least on the wiring using a solution ~~ejection means~~ ejector, and

~~a step of~~ etching the wiring using an atmospheric-pressure plasma device having a linear plasma ~~generation means~~ generator using the resist mask as a mask.

4. (Currently Amended) The method for producing the semiconductor device in any one of claim 1 to claim 3, ~~characterized in that~~ wherein the solution ~~ejection means~~ ejector has one or more of solution ejection ports.

5. (Currently Amended) The method for producing the semiconductor device in any one of claim 1 to claim 3, ~~characterized in that~~ wherein when a wiring material, or a resist, or the like is ejected using the solution ~~ejection means~~ ejector, a substrate is heated.

6. (Currently Amended) The method for producing the semiconductor device in any one of claim 1 to claim 3, ~~characterized in that~~ wherein the etching and/or ashing are/is processed at the atmospheric pressure or near-atmospheric pressure.

7. (Currently Amended) A method for producing a display device using a semiconductor device ~~characterized by having a step of~~ comprising:

forming wiring using a first solution ~~ejection means~~ ejector for ejecting a conductive material,

~~a step of~~ forming a resist mask on the wiring using a second solution ~~ejection means~~ ejector, and

~~a step of~~ etching the wiring using an atmospheric-pressure plasma device having a linear plasma ~~generation means~~ generator using the resist mask as a mask.

8. (Currently Amended) A method for producing a display device using a semiconductor device ~~characterized by having a step of~~ comprising:

forming wiring using a solution ~~ejection means~~ ejector for ejecting a conductive material,

~~a step of~~ forming a resist mask at least on the wiring, and

~~a step of~~ etching the wiring using an atmospheric-pressure plasma device having a linear plasma ~~generation means~~ generator using the resist mask as a mask.

9. (Currently Amended) A method for producing a display device using a semiconductor device ~~characterized by having a step of~~ comprising:

forming wiring,
~~a step of forming a resist mask at least on the wiring using a solution ejection means~~
ejector, and
~~a step of etching the wiring using an atmospheric-pressure plasma device having a~~
linear plasma ~~generation means~~ generator using the resist mask as a mask.

10. (Currently Amended) The method for producing the display device using the semiconductor device in any one of claim 7 to claim 9, ~~characterized in that~~ wherein the solution ~~ejection means~~ ejector has one or more of solution ejection ports.

11. (Currently Amended) The method for producing the display device using the semiconductor device in any one of claim 7 to claim 9, ~~characterized in that~~ wherein when a solution is ejected using the solution ~~ejection means~~ ejector, a substrate is heated.

12. (Currently Amended) The method for producing the display device using the semiconductor device in any one of claim 7 to claim 8, ~~characterized in that~~ wherein the etching and/or the ashing are/is processed at the atmospheric pressure or near-atmospheric pressure.

13. (Currently Amended) A method for producing a semiconductor device
~~characterized by having a step of comprising:~~
forming wiring using a first solution ejection means ejector for ejecting a conductive material,
~~a step of forming a resist mask on the wiring using a second solution ejection means~~
ejector, and
~~a step of etching the wiring using an atmospheric-pressure plasma device having a~~
plurality of linearly-arranged ~~plasma generation means~~ plasma generators using the resist mask as a mask.

14. (Currently Amended) A method for producing a semiconductor device
~~characterized by having a step of comprising:~~

forming wiring using a solution ejection means ejector for ejecting a conductive material,
~~a step of~~ forming a resist mask at least on the wiring, and
~~a step of~~ etching the wiring using an atmospheric-pressure plasma device having a plurality of linearly-arranged ~~plasma-generation means~~ plasma generators using the resist mask as a mask.

15. (Currently Amended) A method for producing a semiconductor device ~~characterized by having a step of comprising:~~
forming wiring,
~~a step of~~ forming a resist mask at least on the wiring using a solution ejection means ejector, and
~~a step of~~ etching the wiring using an atmospheric-pressure plasma device having a plurality of linearly-arranged ~~plasma-generation means~~ plasma generators using the resist mask as a mask.

16. (Currently Amended) The method for producing the semiconductor device in any one of claim 13 to claim 15, ~~characterized in that~~ wherein the solution ~~ejection means ejector~~ has one or more of solution ejection ports.

17. (Currently Amended) The method for producing the semiconductor device in any one of claim 13 to claim 15, ~~characterized in that~~ wherein when a wiring material, or a resist, or the like is ejected using the solution ~~ejection means ejector~~, a substrate is heated.

18. (Currently Amended) The method for producing the semiconductor device in any one of claim 13 to claim 15, ~~characterized in that~~ wherein the etching is processed at the atmospheric pressure or near-atmospheric pressure.

19. (Currently Amended) A method for producing a display device using a semiconductor device ~~characterized by having a step of comprising:~~
forming wiring using a first solution ejection means ejector for ejecting a conductive

material,

~~a step of forming a resist mask on the wiring using a second solution ejection means ejector,~~ and

~~a step of etching the wiring using an atmospheric-pressure plasma device having a plurality of linearly-arranged plasma-generation means~~ plasma generators using the resist mask as a mask.

20. (Currently Amended) A method for producing a display device using a semiconductor device ~~characterized by having a step of comprising:~~

forming wiring using a solution ~~ejection means ejector~~ for ejecting a conductive material,

~~a step of forming a resist mask at least on the wiring, and~~

~~a step of etching the wiring using an atmospheric-pressure plasma device having a plurality of linearly-arranged plasma-generation means~~ plasma generators using the resist mask as a mask.

21. (Currently Amended) A method for producing a display device using a semiconductor device ~~characterized by having a step of comprising:~~

forming wiring,

~~a step of forming a resist mask at least on the wiring using a solution ejection means ejector,~~ and

~~a step of etching the wiring using an atmospheric-pressure plasma device having a plurality of linearly-arranged plasma-generation means~~ plasma generators using the resist mask as a mask.

22. (Currently Amended) A method for producing the display device using the semiconductor device in any one of claim 19 to claim 21, ~~characterized in that wherein the solution ejection means ejector~~ has one or more of solution ejection ports.

23. (Currently Amended) A method for producing the display device using the semiconductor device in any one of claim 19 to claim 21, ~~characterized in that wherein~~ when

a solution is ejected using the solution ~~ejection means~~ ejector, a substrate is heated.

24. (Currently Amended) A method for producing the display device using the semiconductor device in any one of claim 19 to claim 21, ~~characterized in that~~ wherein the etching is processed at the atmospheric pressure or near-atmospheric pressure.